

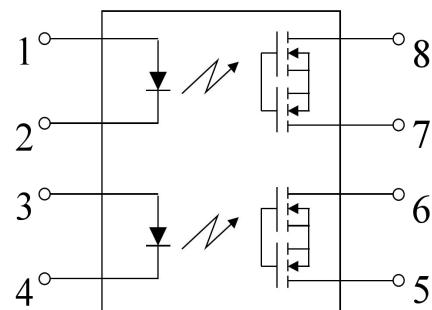


JOR212D4 JOR212D8

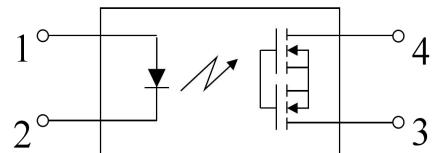
Description

The JOR212D4 and JOR212D8 consists of a AlGaAs infrared emitting diode input stage optically coupled to a high-voltage output detector circuit. The detector consists of a high-speed photovoltaic diode array and driver circuitry to switch on/off two discrete high voltage MOSFETs.

Block Diagram and Package



1, 3: Anode (LED)
2, 4: Cathode (LED)
5, 6, 7, 8: Drain (MOS FET)



1: Anode (LED)
2: Cathode (LED)
3, 4: Drain (MOS FET)

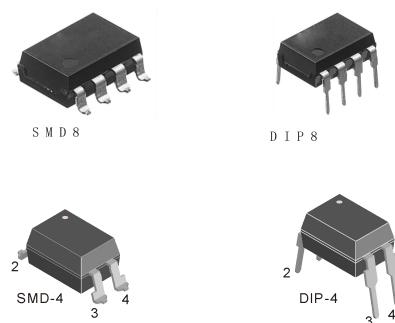
Features

- Normally opened (1-Form-A)
- Control 60V AC or DC voltage
- Switch 500 mA load
- Control low level analog signal
- High sensitivity, low conductivity resistance
- High isolation voltage 5 KV (DIP/SMD)
- Pb free and RoHS compliant

PACKAGE OUTLINE

Application

- Communications products (personal computers, laptops)
- Modem/sensor
- Mobile phones/security equipment
- Measuring and testing equipment
- Plant automation equipment
- High-speed inspection machines



ORDERING AND MARKING INFORMATION	
MARKING INFORMATION	
ORDERING INFORMATION	LABEL INFORMATION
JOR212DX(Y)(Z)-G JOR – Company Abbr 212 – Part Number D – DIP or SMD Package X – 4 or 8(Pin Count) Y – Lead Form Option (M/S/SL/None) Z – Tape and Reel Option (T1/T2) G – Green	 <p>JOR : Company Abbr. 212 : Part Number Y : Fiscal Year A : Manufacturing Code WW : Work Week</p>

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Parameter		Symbol	Rating	Unit	Parameter
Input	Input forward current	I_F	50	mA	
	Input reverse voltage	V_R	3	V	
	Input forward current (pulsed)	I_{FP}	1	A	$f=100 \text{ Hz}$ Duty cycle= 0.1%
	Input power dissipation	P	75	mW	
Output	OFF-state output terminal voltage	V_L	60	V	
	ON-state current	I_L	0.5	A	
	Peak leakage current	I_{peak}	1.5	A	100 ms (1 shot), $V_L= \text{DC}$
	Output power dissipation	P_{out}	800 500	mW	DIP8 SMD8 DIP4 SMD4
I/O Isolation voltage		V_{iso}	5,000	VAC	DIP SMD
Limit temperature	Operating temperature	T_{opr}	$-40^\circ\text{C} \sim + 85^\circ\text{C}$	$^\circ\text{C}$	Do not freeze at low temperatures
	Storage temperature	T_{stg}	$-40^\circ\text{C} \sim + 100^\circ\text{C}$		

Electro-optical Characteristics ($T_a=25^\circ\text{C}$)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Input	Trigger LED current	I_{Fon}	$I_L=0.5\text{A}$	0.5	1.2	3	mA
	Return LED current	I_{Foff}	$I_L=0.5\text{A}$	0	1.0	3	mA
	Input Forward Voltage	V_F	$I_F=5\text{mA}$	1	1.3	1.4	V
Output	Output On-resistance	R_{on}	$I_F=5\text{mA}, I_L=0.5\text{A},$ Electricity less than 1 second	0	0.8	1.5	Ω
	Output Leakage Current	I_{Leak}	$I_F=0\text{mA}, V_L=60\text{V}$	-100	100	1000	nA
Transfer Characteristics	Turn-on time	T_{on}	$I_F=5\text{mA}, I_L=0.5\text{A}$	200	890	2000	us
	Turn-off time	T_{off}	$I_F=5\text{mA}, I_L=0.5\text{A}$	50	210	1000	us
	Input-Output Capacitance	C_{iso}	$f=1\text{MHz}, V_B=0$		0.8	1.5	pF
	Isolation Resistance	R_{iso}	500V DC	1,000			$M\Omega$

Note: Recommended values for LED forward current $I_F=5$ to 10 mA

Typical Performance Curves

Fig.1 ON-state current vs Ambient Temperature

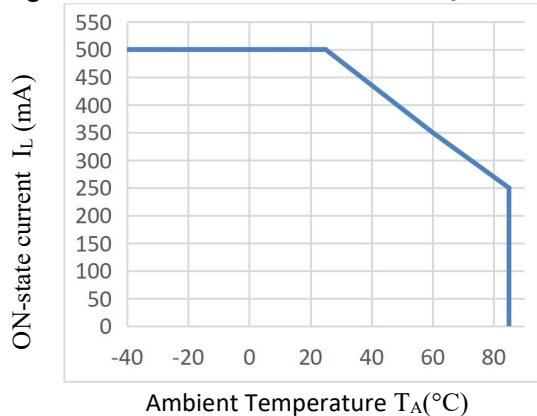
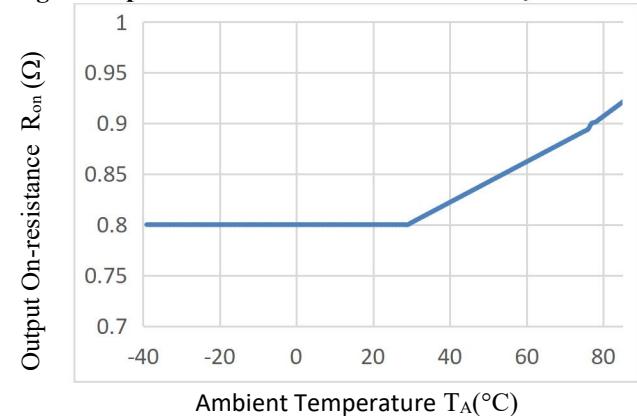


Fig.2 Output On-resistance vs. Ambient Temperature



JOR212D4 JOR212D8

Fig.3 Turn-on time vs Ambient Temperature

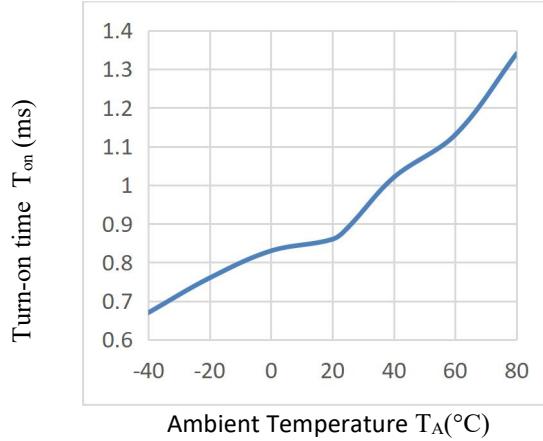


Fig.4 Turn-off time vs Ambient Temperature

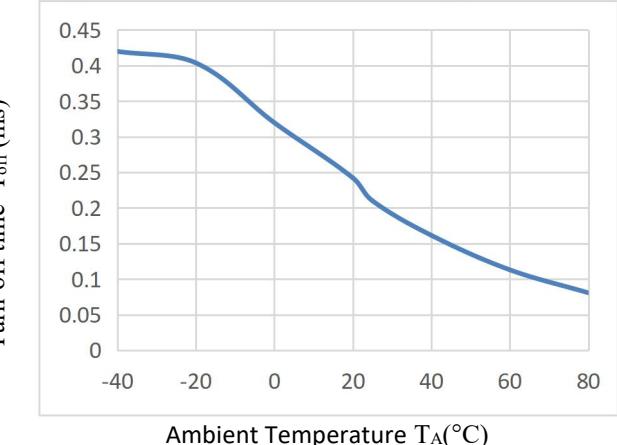


Fig.5 Trigger LED current vs Ambient Temperature

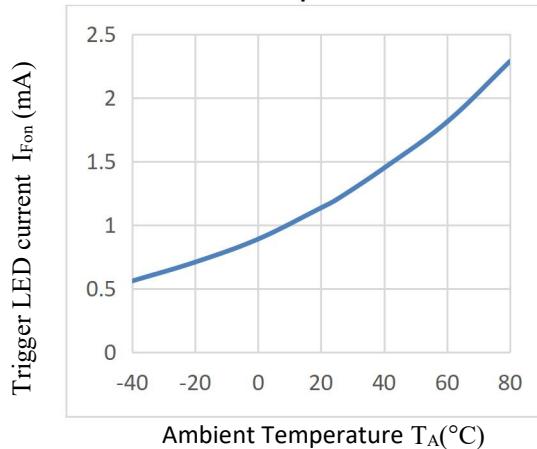


Fig.6 Return LED current vs Ambient Temperature

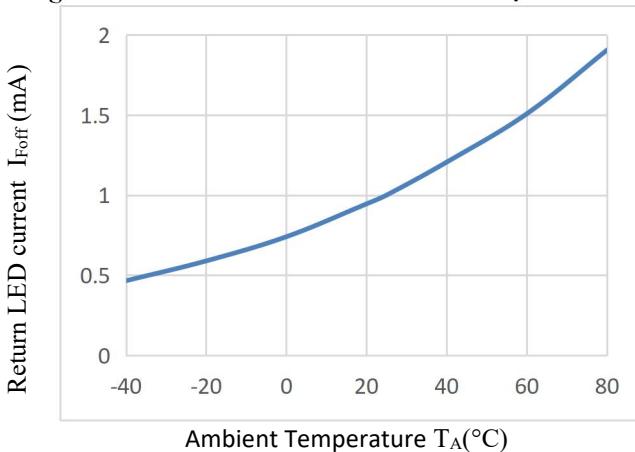


Fig.7 Forward Voltage vs Ambient Temperature

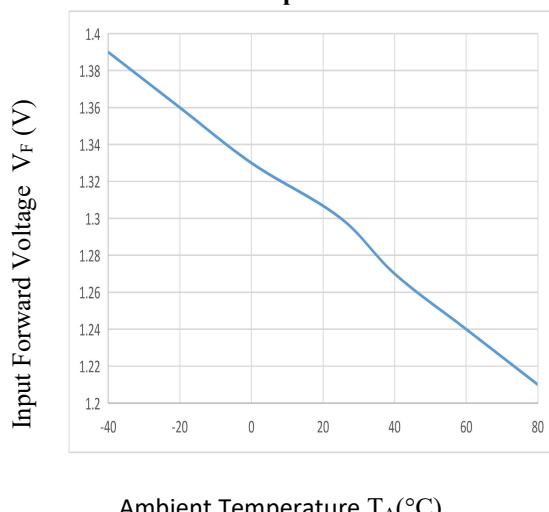
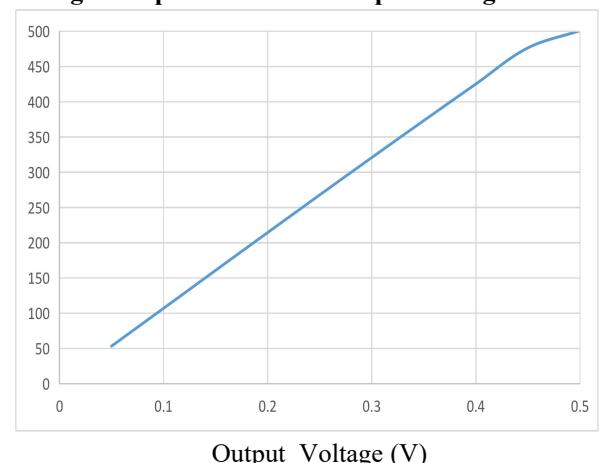


Fig.8 Output Current vs Output Voltage



JOR212D4 JOR212D8

Fig.9 Output Leakage Current vs OFF-state output terminal voltage

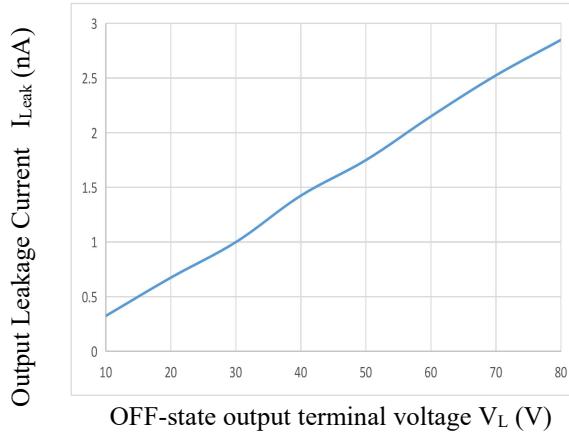


Fig.10 Turn-on time vs Input Forward Current

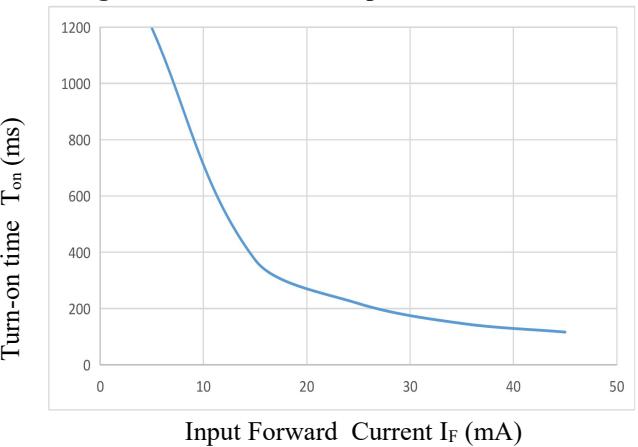
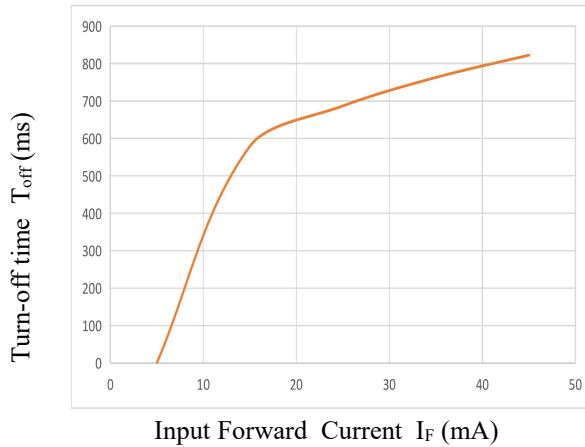
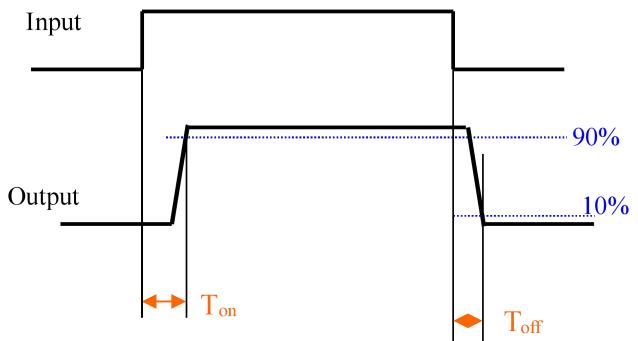


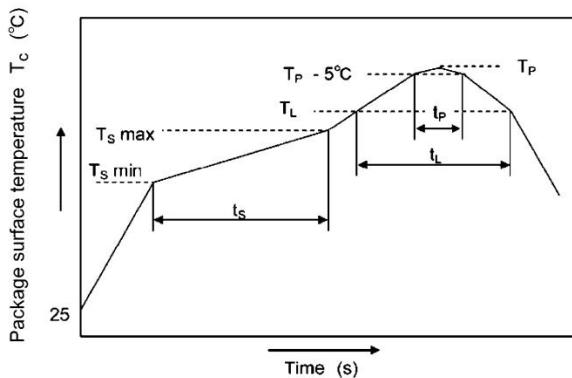
Fig.11 Turn-off time vs Input Forward Current



★ Turn-on time and Turn-off time



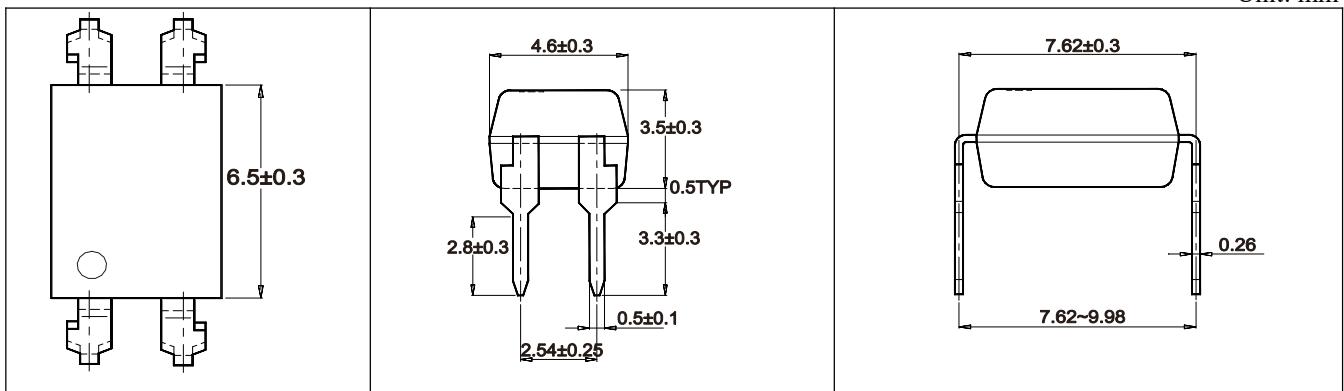
Solder Reflow Profile



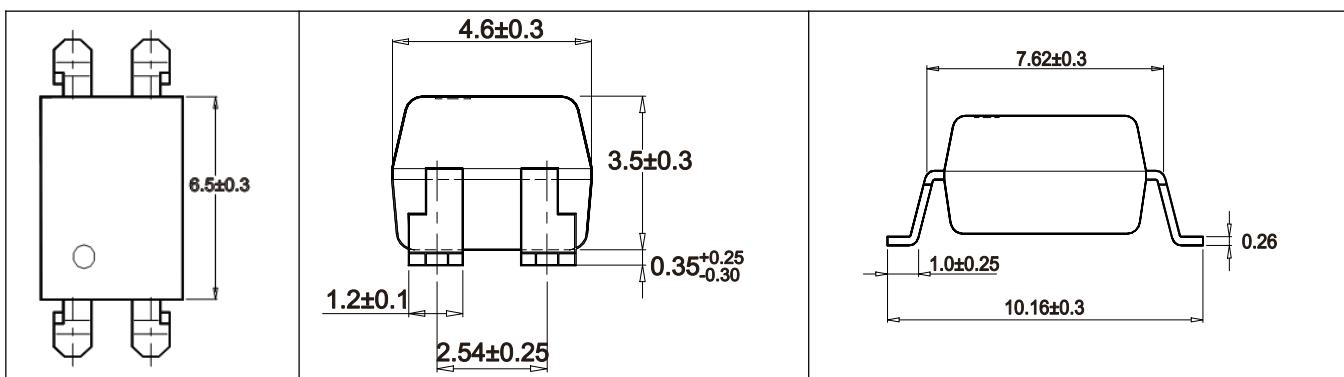
	Symbol	Min	Max	Unit
Preheat temperature	T_S	150	200	°C
Preheat time	t_S	60	120	s
Ramp-up rate (T_L to T_P)			3	°C/s
Liquidus temperature	T_L	217		°C
Time above T_L	t_L	60	150	s
Peak temperature	T_P		260	°C
Time during which T_c is between ($T_P - 5$) and T_P	t_P		30	s
Ramp-down rate (T_P to T_L)			6	°C/s

Outline Dimensions

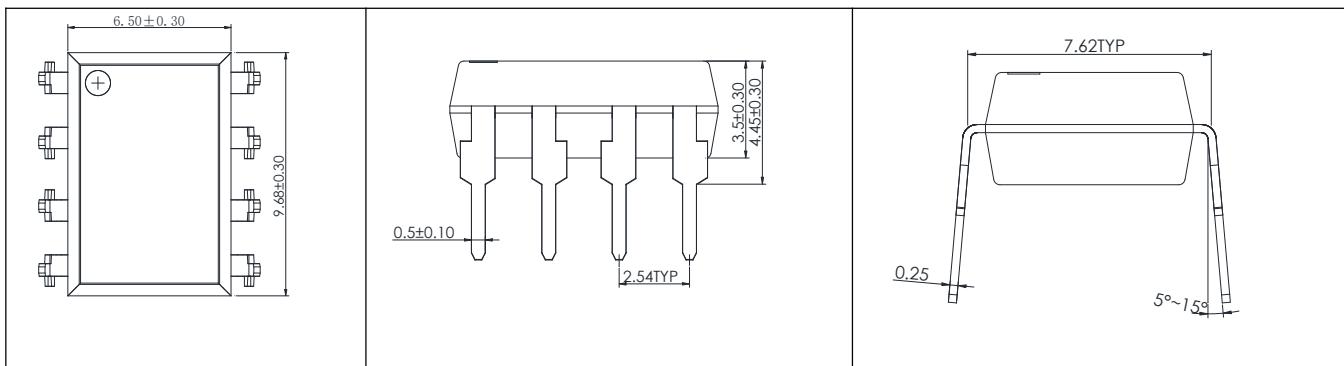
Unit: mm



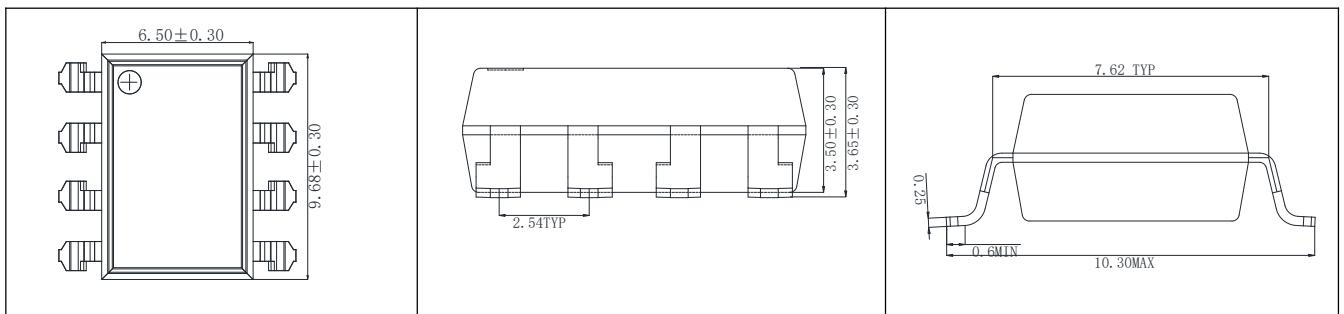
4-pin DIP



4-pin SMD



8-pin DIP



8pin SMD

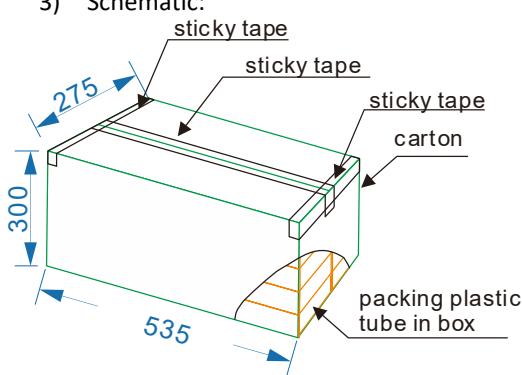
Packing

■ Summary table

Package Type	Packing Form	Quantity per Reel	Quantity per Box	Quantity per Carton	Antistatic Bag Specification	Box Specification	Carton Specification	Note
SMD-8	Reel ($\phi 330\text{mm}$ Blue)	1K pcs/reel	2 reels/box	10 boxes/ctn	380*380mm	340*60*340 mm	620*360*365 mm	Guard band 200mm min.
SMD-4	Reel($\phi 330\text{mm}$ Blue)	2K pcs/reel	2 reels/box	10 boxes/ctn	380*380mm	340*60*340 mm	620*360*365 mm	
DIP-8	Tube ($500*12*11\text{mm}$)	45 pcs /tube	50 tubes/box	10 boxes /ctn	NA	525*128*56 mm	535*275*300 mm	Endplug (blue) and Endplug (white) keep the direction
DIP-4	Tube ($500*12*11\text{mm}$)	100pcs /tube	50 tubes/box	10 boxes /ctn	NA	525*128*56 mm	535*275*300 mm	

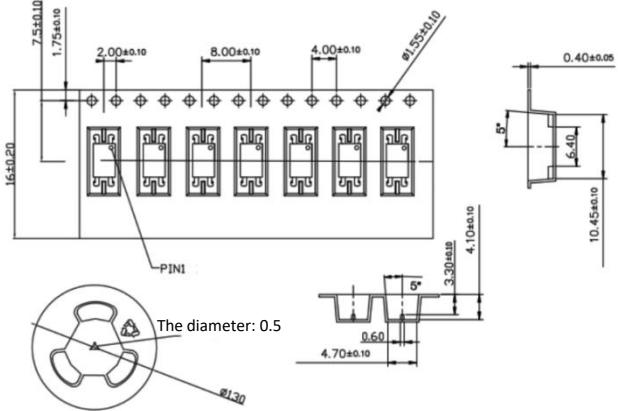
■ DIP-4 (tube)

- 1) Qty/ctn: 50000pcs
- 2) Inner packing:
 - i. 100pcs/tube, antistatic tube, indication of trade mark and antistatic.
 - ii. 50 tubes/box.
- 3) Schematic:



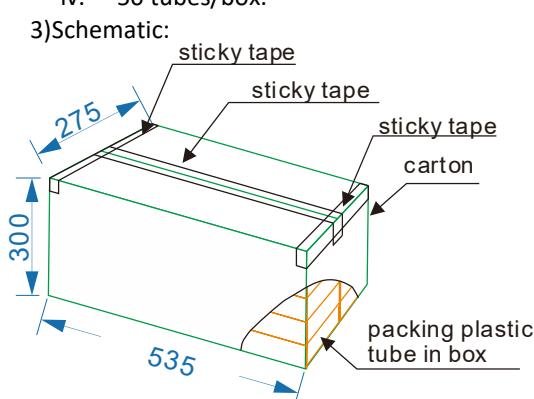
■ SMD-4 (Tape & Reel)

- 1) Qty/reel: 2000 pcs. Qty/ctn: 40000 pcs.
- 2) Inner packing: 2000pcs/reel.
- 3) Schematic:



■ DIP-8(tube)

- 1) Qty/ctn: 22500pcs.
- 2) Inner packing:
 - iii. 45pcs/tube, antistatic tube, indication of trade mark and antistatic.
 - iv. 50 tubes/box.
- 3)Schematic:



■ SMD-8 (Tape & Reel)

- i. Qty/reel: 1000 pcs. Qty/ctn: 20000 pcs.
- ii. Inner packing: 1000pcs/reel.
- iii. Schematic:

